

Standard Rectifier

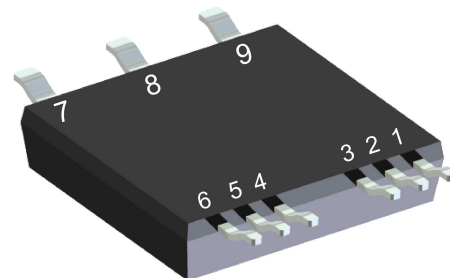
3~ Rectifier	
V_{RRM}	= 1800 V
I_{DAV}	= 90 A
I_{FSM}	= 350 A

ISOPLUS™
 Surface Mount Power Device
 3~ Rectifier Bridge

Part number

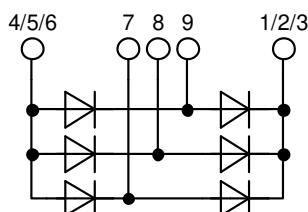
DMA90U1800LB

Marking on Product: DMA90U1800LB



Backside: isolated

 E72873



Features / Advantages:

- Rectifier diode
- Isolated back surface
- Low coupling capacity between pins and heatsink
- Enlarged creepage towards heatsink
- Application friendly pinout
- Low inductive current path
- High reliability

Applications:

- Line rectifying 50/60 Hz
- Drives
- SMPS
- UPS

Package: SMPD

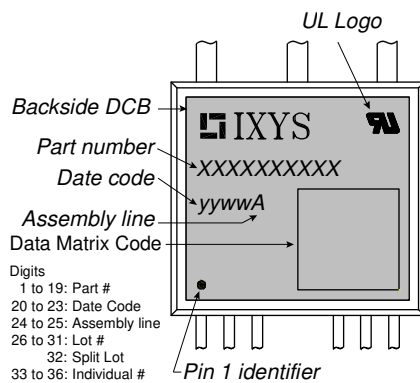
- Isolation Voltage: 3000 V~
- Industry convenient outline
- RoHS compliant
- Epoxy meets UL 94V-0
- Soldering pins for PCB mounting
- Backside: DCB ceramic
- Reduced weight
- Advanced power cycling

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Rectifier				Ratings			
Symbol	Definition	Conditions		min.	typ.	max.	Unit
V_{RSM}	max. non-repetitive reverse blocking voltage	$T_{VJ} = 25^{\circ}\text{C}$				1900	V
V_{RRM}	max. repetitive reverse blocking voltage	$T_{VJ} = 25^{\circ}\text{C}$				1800	V
I_R	reverse current	$V_R = 1800\text{ V}$	$T_{VJ} = 25^{\circ}\text{C}$			40	μA
		$V_R = 1800\text{ V}$	$T_{VJ} = 150^{\circ}\text{C}$			1.5	mA
V_F	forward voltage drop	$I_F = 30\text{ A}$	$T_{VJ} = 25^{\circ}\text{C}$			1.26	V
		$I_F = 90\text{ A}$				1.79	V
		$I_F = 30\text{ A}$	$T_{VJ} = 150^{\circ}\text{C}$			1.20	V
		$I_F = 90\text{ A}$				1.93	V
I_{DAV}	bridge output current	$T_C = 110^{\circ}\text{C}$ rectangular	$T_{VJ} = 175^{\circ}\text{C}$ $d = \frac{1}{3}$			90	A
V_{F0}	threshold voltage	} for power loss calculation only		$T_{VJ} = 175^{\circ}\text{C}$		0.81	V
r_F	slope resistance					12.7	m Ω
R_{thJC}	thermal resistance junction to case					1.1	K/W
R_{thCH}	thermal resistance case to heatsink				0.4		K/W
P_{tot}	total power dissipation	$T_C = 25^{\circ}\text{C}$				135	W
I_{FSM}	max. forward surge current	$t = 10\text{ ms}; (50\text{ Hz}), \text{ sine}$	$T_{VJ} = 45^{\circ}\text{C}$			350	A
		$t = 8,3\text{ ms}; (60\text{ Hz}), \text{ sine}$	$V_R = 0\text{ V}$			380	A
		$t = 10\text{ ms}; (50\text{ Hz}), \text{ sine}$	$T_{VJ} = 150^{\circ}\text{C}$			300	A
		$t = 8,3\text{ ms}; (60\text{ Hz}), \text{ sine}$	$V_R = 0\text{ V}$			320	A
I^2t	value for fusing	$t = 10\text{ ms}; (50\text{ Hz}), \text{ sine}$	$T_{VJ} = 45^{\circ}\text{C}$			615	A ² s
		$t = 8,3\text{ ms}; (60\text{ Hz}), \text{ sine}$	$V_R = 0\text{ V}$			600	A ² s
		$t = 10\text{ ms}; (50\text{ Hz}), \text{ sine}$	$T_{VJ} = 150^{\circ}\text{C}$			450	A ² s
		$t = 8,3\text{ ms}; (60\text{ Hz}), \text{ sine}$	$V_R = 0\text{ V}$			425	A ² s
C_J	junction capacitance	$V_R = 400\text{ V}; f = 1\text{ MHz}$			11		pF

Package SMPD				Ratings			
Symbol	Definition	Conditions		min.	typ.	max.	Unit
I _{RMS}	RMS current	per terminal				100	A
T _{VJ}	virtual junction temperature			-55		175	°C
T _{op}	operation temperature			-55		150	°C
T _{stg}	storage temperature			-55		150	°C
Weight					8.5		g
F _C	mounting force with clip			40		130	N
d _{Spp/App}	creepage distance on surface / striking distance through air	terminal to terminal		1.6			mm
d _{Spb/Apb}		terminal to backside		4.0			mm
V _{ISOL}	isolation voltage	t = 1 second	50/60 Hz, RMS; I _{ISOL} ≤ 1 mA	3000			V
		t = 1 minute		2500			V



Part description

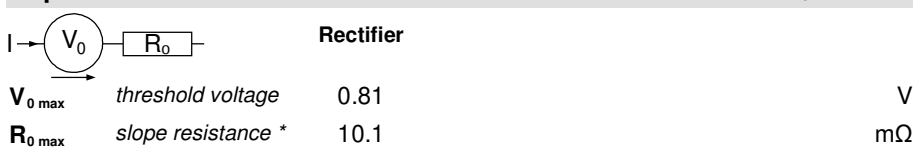
D = Diode
 M = Standard Rectifier
 A = (up to 1800V)
 90 = Current Rating [A]
 U = 3- Rectifier Bridge
 1800 = Reverse Voltage [V]
 LB = SMPD-B

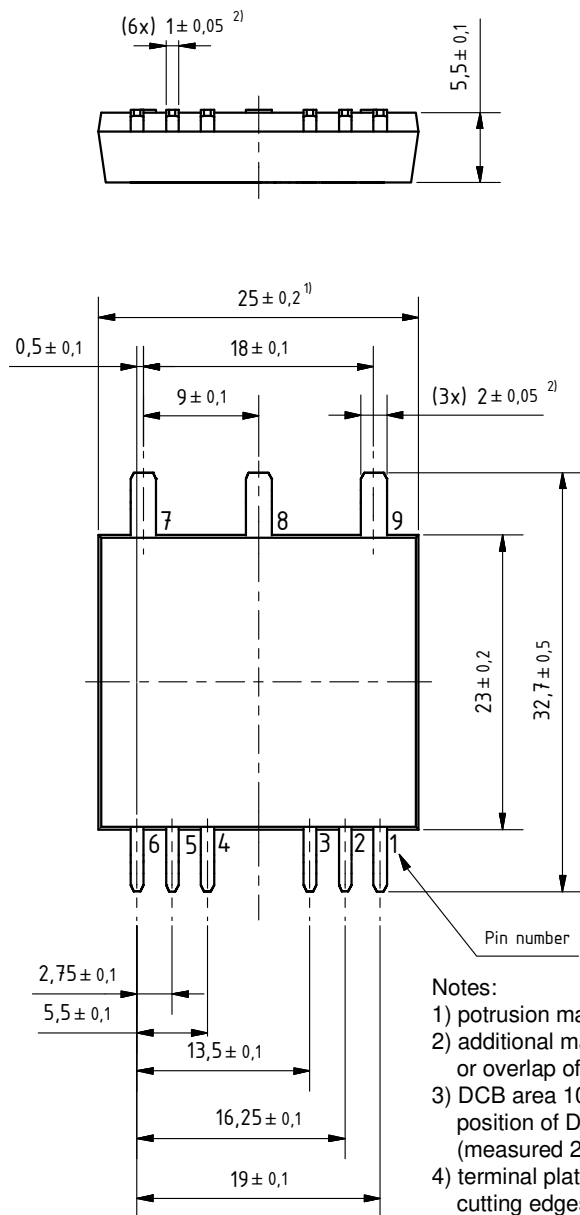
Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	DMA90U1800LB-TUB	DMA90U1800LB	Tube	20	517130
Alternative	DMA90U1800LB-TRR	DMA90U1800LB	Tape & Reel	200	524497

Equivalent Circuits for Simulation

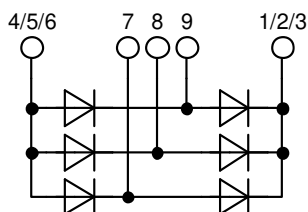
* on die level

$T_{VJ} = 175^\circ\text{C}$



Outlines SMPD
A (8 : 1)

Notes:

- 1) potrusion may add 0.2 mm max. on each side
- 2) additional max. 0.05 mm per side by punching misalignement or overlap of dam bar or bending compression
- 3) DCB area 10 to 50 μm convex;
position of DCB area in relation to plastic rim: $\pm 25 \mu\text{m}$ (measured 2 mm from Cu rim)
- 4) terminal plating: 0.2 - 1 μm Ni + 10 - 25 μm Sn (gal v.)
cutting edges may be partially free of plating



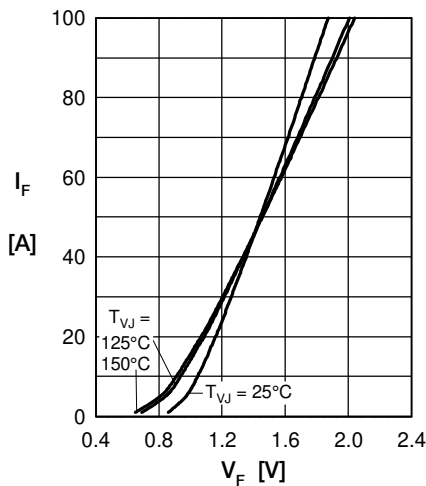
Rectifier


Fig. 1 Forward current vs. voltage drop per diode

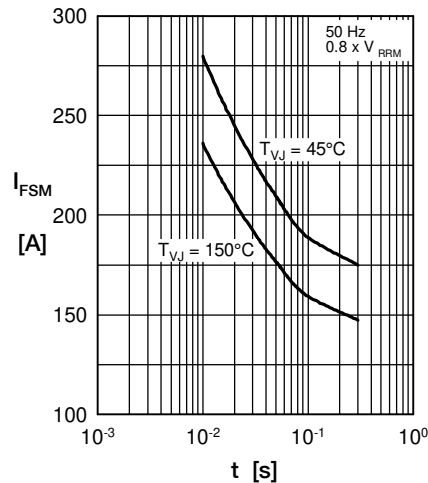


Fig. 2 Surge overload current vs. time per diode

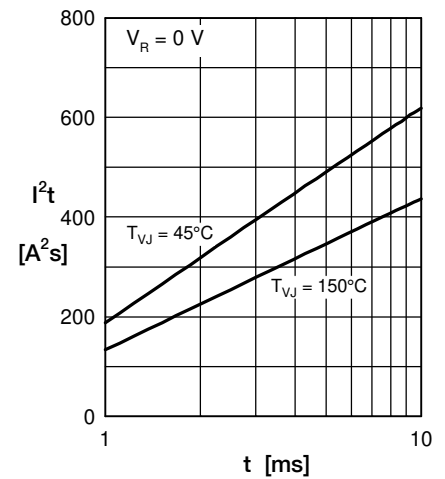


Fig. 3 I^2t vs. time per diode

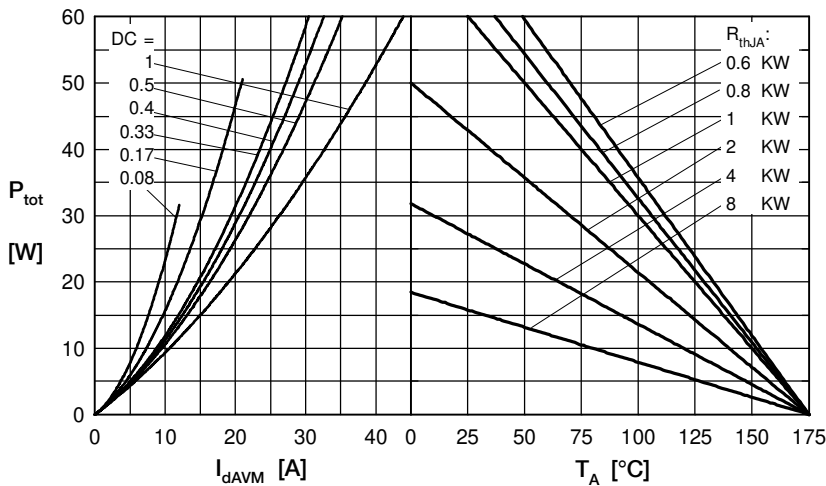


Fig. 4 Power dissipation vs. forward current and ambient temperature per diode

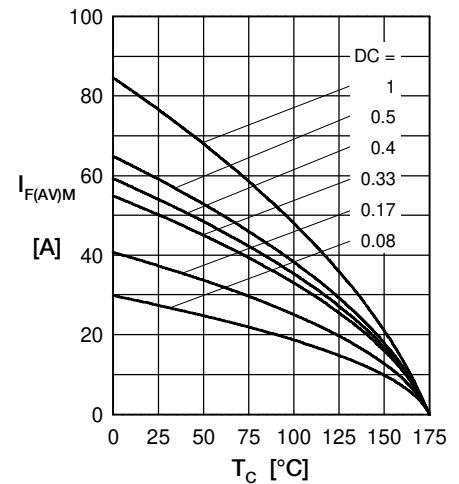


Fig. 5 Max. forward current vs. case temperature per diode

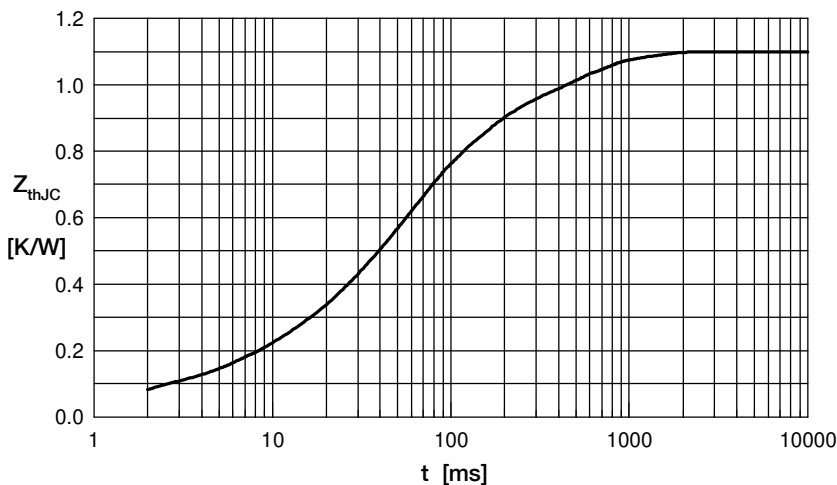


Fig. 6 Transient thermal impedance junction to case vs. time per diode

Constants for Z_{thJC} calculation:

i	R_{th} (K/W)	t_i (s)
1	0.030	0.0003
2	0.072	0.0045
3	0.092	0.0530
4	0.606	0.0520
5	0.300	0.4000